

/ Descriptions

TO-277
TO-277 Plastic package Ultrafast Recovery Diode.

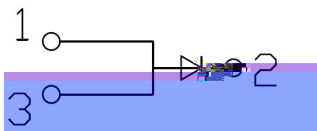
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability. HF Product.

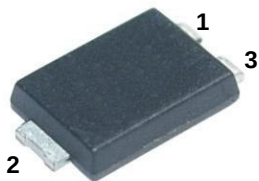
/ Applications

For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.

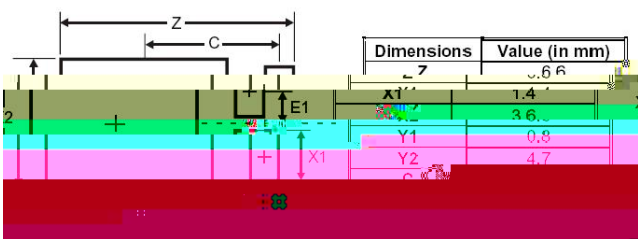
/ Equivalent Circuit



/ Pinning



PIN1 Anode PIN 2 Cathode PIN 3 Anode



Suggested Pad layout

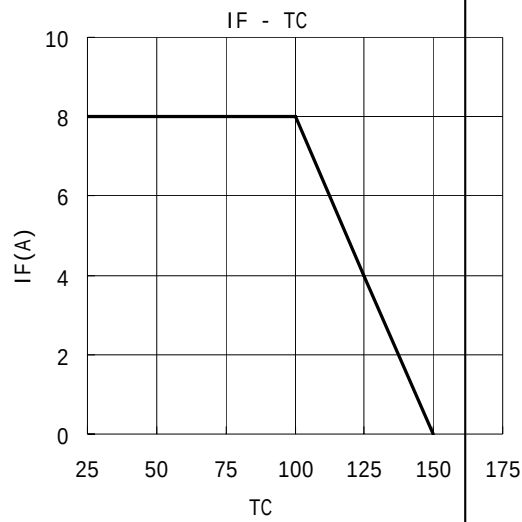
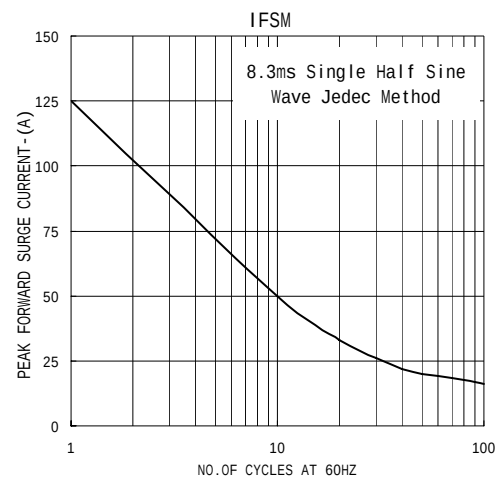
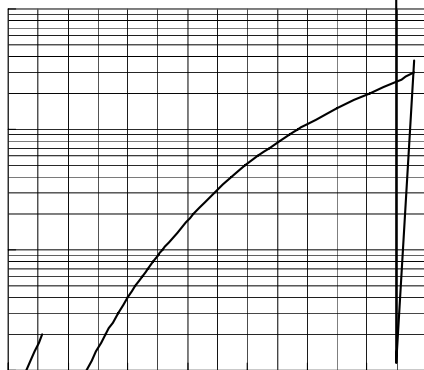
/ h_{FE} Classifications & Marking

See Marking Instructions.

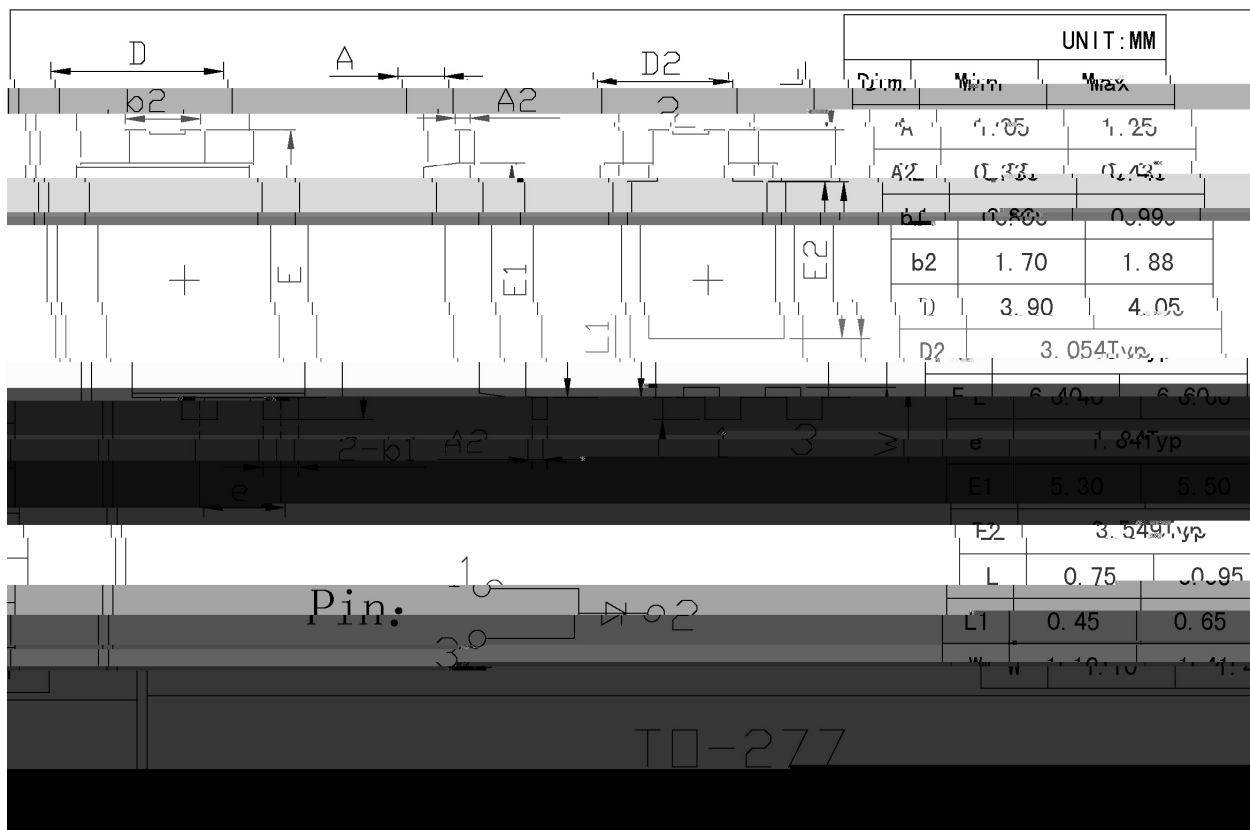
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Reverse voltage	V_{RMS}	420	V
Average Rectified Forward Current	I_F	8	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	125	A
Thermal Resistance Junction to Case	R_{JC}	3.5	/W
Junction and Storage Temperature Range	T_j T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_{BR}	$I_R=100\mu A$	600			V
Forward voltage	V_F	$I_F=8A$ $T_c=25$		1.4	1.7	V
		$I_F=16A$ $T_c=25$		1.7	2.1	V
		$I_F=8A$ $T_c=125$		1.4	1.7	V
Instantaneous Reverse Current	I_R Note 1	$V_R=600V$ $T_a=25$			5	μA
		$V_R=480V$ $T_a=125$			300	μA
		$V_R=600V$ $T_a=125$			500	μA

/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



MUR860

Note:

MUR860 Product Type.

****: Lot No. Code, code change with Lot No.

